

## Timing properties of the RD50-MPW2 CMOS detector

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The CERN-RD50 collaboration has been developing High Voltage CMOS detector prototypes for high radiation environment based on high resistivity substrate and large collection electrode. In this contribution we will present timing properties of the RD50-MPW2 chip manufactured in LFoundry 150 nm process, which features an active 8 x 8 matrix of pixels with an analog front end and discriminator circuit. The time resolution and time walk of the detector were evaluated before and after neutron irradiation. Charge in the sensor was generated by laser TCT with light injection from the edge and back side.

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